

**AMENDMENT**

In the Claims

Please cancel claim 25 and amend claims 1 and 26, so that the claims read as follows:

1. (Currently Amended) A method for cleaning silicon carbide materials on a large scale, the method comprising the acts of:

using an integrated system that is adapted for handling a multiplicity of said silicon carbide materials during said cleaning;

ultrasonicing said silicon carbide materials in an aqueous solution of inorganic acid;

ultrasonicing said silicon carbide materials in a bath of deionized water; and

purging at least one opening within each of said silicon carbide materials using an inert gas stream during ultrasonicing of said silicon carbide materials in the aqueous solution.

2. (Original) The method of Claim 1, wherein said silicon carbide materials are sintered.

3. (Original) The method of Claim 1, wherein said silicon carbide materials are formed using chemical vapor deposition (CVD).